



Application Specific Discretes
A.S.D.

ESDA6V1P6

QUAD TRANSIL™ ARRAY FOR ESD PROTECTION

MAIN APPLICATIONS

Where transient overvoltage protection in ESD sensitive equipment is required, such as :

- Computers
- Printers
- Communication systems and cellular phones
- Video equipment

This device is particularly adapted to the protection of symmetrical signals.

FEATURES

- 4 UNIDIRECTIONAL TRANSIL™ FUNCTIONS.
- BREAKDOWN VOLTAGE $V_{BR} = 6.1V$ MIN
- LOW LEAKAGE CURRENT < 500 nA
- VERY SMALL PCB AREA < 2.6 mm²

DESCRIPTION

The ESDA6V1P6 is a monolithic array designed to protect up to 4 lines against ESD transients.

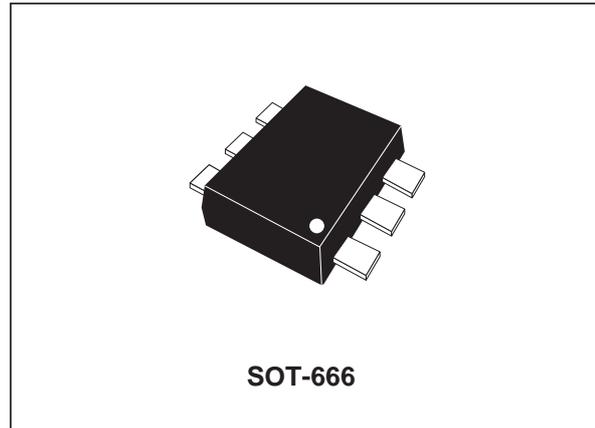
This device is ideal for applications where board space saving is required.

BENEFITS

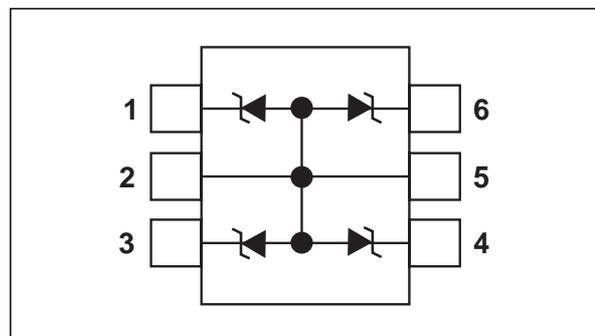
- High ESD protection level.
- High integration.
- Suitable for high density boards.

COMPLIES WITH THE FOLLOWING STANDARDS :

- IEC61000-4-2 level 4: 15 kV (air discharge)
8 kV (contact discharge)
- MIL STD 883E-Method 3015-7: class 3
25kV HBM (Human Body Model)



FUNCTIONAL DIAGRAM



ESDA6V1P6

ABSOLUTE RATINGS (T_{amb} = 25°C)

Symbol	Parameter	Test conditions	Value	Unit
V _{PP}	ESD discharge - IEC61000-4-2 air discharge IEC61000-4-2 contact discharge		± 15 ± 8	kV
P _{PP}	Peak pulse power (8/20 μs) (see note 1)	T _j initial = T _{amb}	150	W
T _j	Junction temperature		125	°C
T _{stg}	Storage temperature range		- 55 to + 150	°C
T _L	Maximum lead temperature for soldering during 10s at 5mm for case		260	°C
T _{op}	Operating temperature range		- 40 to + 150	°C

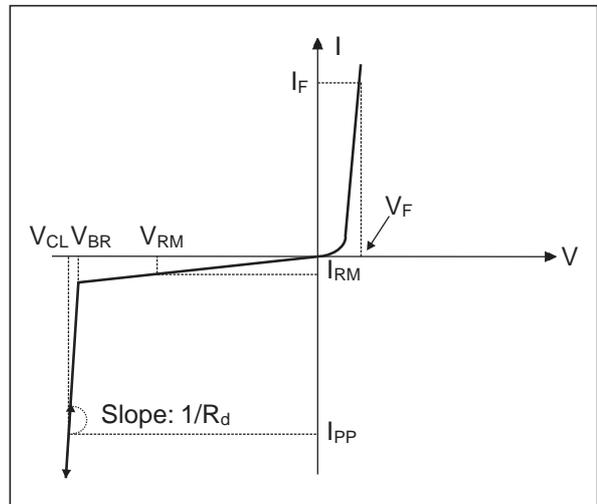
Note 1: for a surge greater than the maximum values, the diode will fail in short-circuit.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient on printed circuit on recommended pad layout	220	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Symbol	Parameter
V _{RM}	Stand-off voltage
V _{BR}	Breakdown voltage
V _{CL}	Clamping voltage
I _{RM}	Leakage current
I _{PP}	Peak pulse current
αT	Voltage temperature coefficient
V _F	Forward voltage drop
C	Capacitance per line
R _d	Dynamic resistance



Types	V _{BR} @		I _r	I _{RM} @		R _d	αT	C
	min.	max.		max.	V _{RM}			
	V	V	mA	μA	V	Ω	10 ⁻⁴ /°C	typ. @ 0V pF
ESDA6V1P6	6.1	7.2	1	0.5	3	1.5	4.5	70

Fig. 1: Relative variation of peak pulse power versus initial junction temperature.

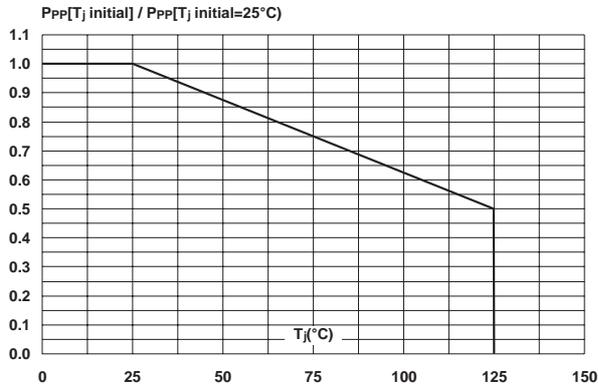


Fig. 2: Peak pulse power versus exponential pulse duration.

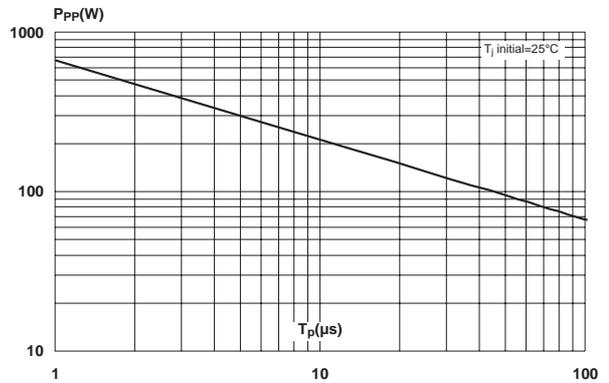


Fig. 3: Clamping voltage versus peak pulse current (typical values, rectangular waveform).

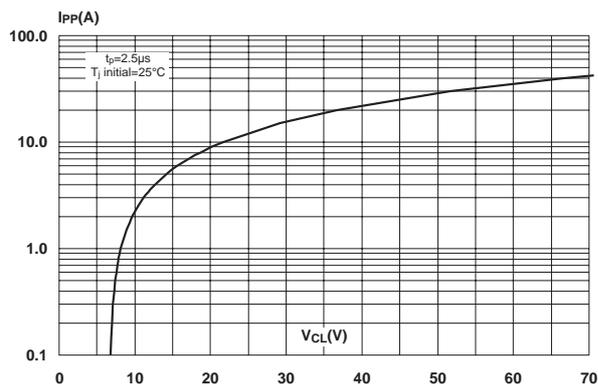


Fig. 4: Forward voltage drop versus peak forward current (typical values).

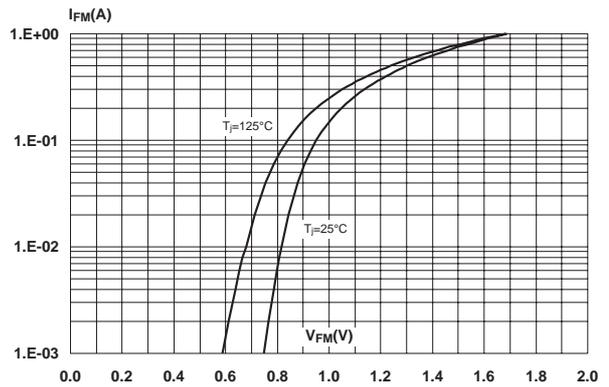


Fig. 5: Junction capacitance versus reverse voltage applied (typical values).

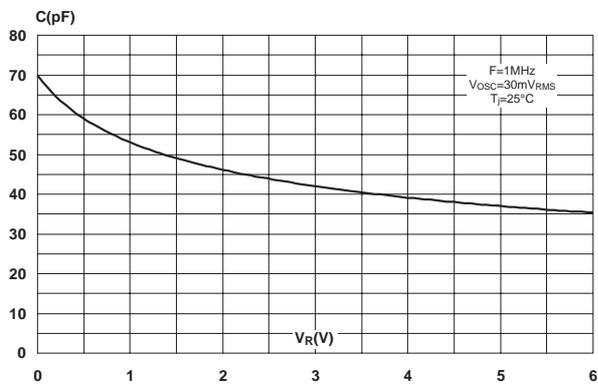
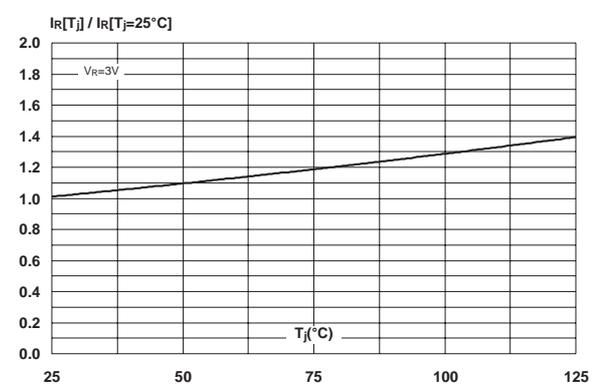
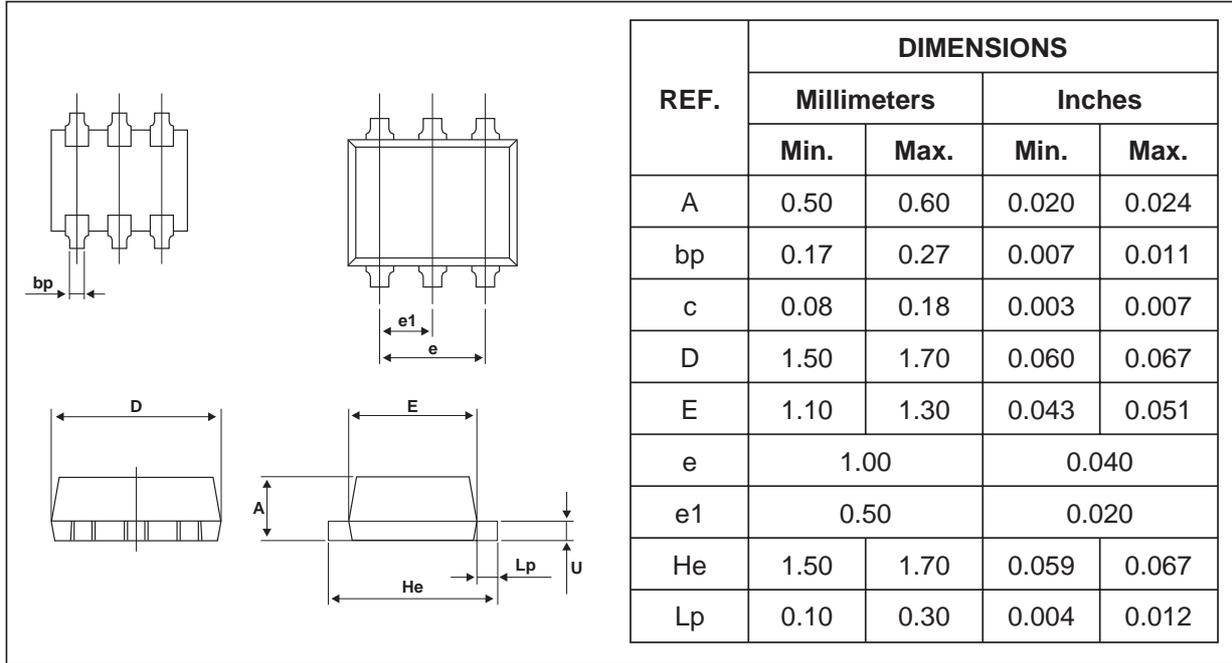


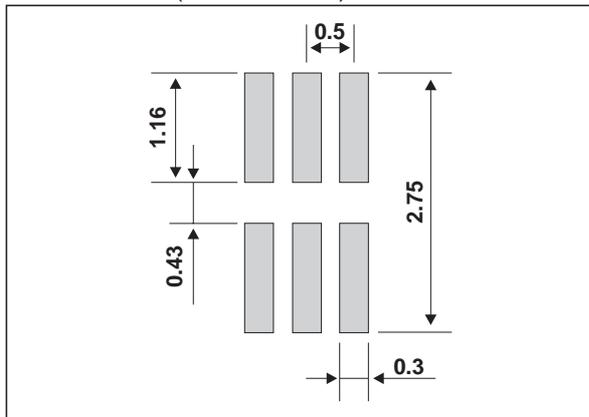
Fig. 6: Relative variation of leakage current versus junction temperature (typical values).



PACKAGE MECHANICAL DATA
SOT-666



FOOT PRINT (in millimeters)



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